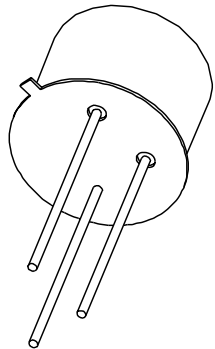


DATA SHEET



BSX32 NPN switching transistor

Product specification
Supersedes data of September 1994
File under Discrete Semiconductors, SC04

1997 May 28

NPN switching transistor

BSX32

FEATURES

- High current (max. 1 A)
- Low voltage (max. 40 V).

APPLICATIONS

- High-current switching in industrial applications.

DESCRIPTION

NPN switching transistor in a TO-39 metal package.

PINNING

PIN	DESCRIPTION
1	emitter
2	base
3	collector, connected to case

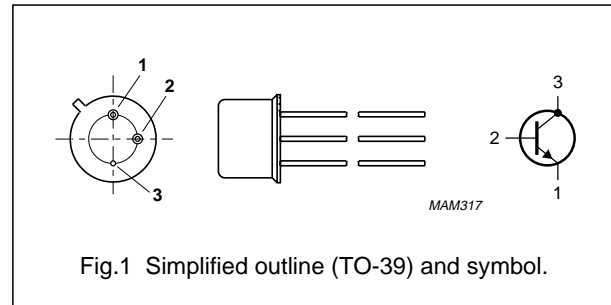


Fig.1 Simplified outline (TO-39) and symbol.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–	65	V
V_{CEO}	collector-emitter voltage	open base	–	–	40	V
I_C	collector current (DC)		–	–	1	A
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ }^\circ\text{C}$	–	–	800	mW
h_{FE}	DC current gain	$I_C = 1\text{ A}; V_{CE} = 5\text{ V}$	20	60	–	
f_T	transition frequency	$I_C = 50\text{ mA}; V_{CE} = 10\text{ V}; f = 100\text{ MHz}$	300	–	–	MHz
t_{off}	turn-off time	$I_{Con} = 500\text{ mA}; I_{Bon} = 50\text{ mA}; I_{Boff} = -50\text{ mA}$	–	–	60	ns

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	65	V
V_{CEO}	collector-emitter voltage	open base	–	40	V
V_{EBO}	emitter-base voltage	open collector	–	6	V
I_C	collector current (DC)		–	1	A
I_{CM}	peak collector current		–	1	A
I_{BM}	peak base current		–	200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$	–	800	mW
		$T_{case} \leq 25\text{ °C}$	–	3.5	W
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	200	°C
T_{amb}	operating ambient temperature		–65	+150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	in free air	219	K/W
$R_{th\ j-c}$	thermal resistance from junction to case		50	K/W

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CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 50\text{ V}$	–	–	4	μA
I_{EBO}	emitter cut-off current	$I_E = 0; V_{EB} = 4\text{ V}$	–	–	300	nA
h_{FE}	DC current gain	$V_{CE} = 1\text{ V}$; note 1 $I_C = 10\text{ mA}$ $I_C = 100\text{ mA}$ $I_C = 500\text{ mA}$	30 60 25	– – 60	– 150 –	
h_{FE}	DC current gain	$I_C = 1\text{ A}; V_{CE} = 5\text{ V}$; note 1	20	60	–	
h_{FE}	DC current gain	$V_{CE} = 1\text{ V}; T_{amb} = -55\text{ }^{\circ}\text{C}$; note 1 $I_C = 100\text{ mA}$ $I_C = 500\text{ mA}$	30 15	– –	– –	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 100\text{ mA}; I_B = 10\text{ mA}$; note 1 $I_C = 500\text{ mA}; I_B = 50\text{ mA}$; note 1 $I_C = 1\text{ A}; I_B = 100\text{ mA}$; note 1	– – –	170 360 600	250 500 850	mV mV mV
V_{BEsat}	base-emitter saturation voltage	$I_C = 100\text{ mA}; I_B = 10\text{ mA}$; note 1 $I_C = 500\text{ mA}; I_B = 50\text{ mA}$; note 1 $I_C = 1\text{ A}; I_B = 100\text{ mA}$; note 1	– – –	800 – –	900 1.5 2	mV V V
C_c	collector capacitance	$I_E = i_e = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	–	–	10	pF
C_e	emitter capacitance	$I_C = i_c = 0; V_{EB} = 500\text{ mV}; f = 1\text{ MHz}$	–	–	55	pF
f_T	transition frequency	$I_C = 50\text{ mA}; V_{CE} = 10\text{ V}; f = 100\text{ MHz}$	300	–	–	MHz
Switching times (between 10% and 90% levels)						
t_{on}	turn-on time	$I_{Con} = 500\text{ mA}; I_{Bon} = 50\text{ mA}$;	–	–	35	ns
t_{off}	turn-off time	$I_{Boff} = -50\text{ mA}$	–	–	60	ns

Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.01$.

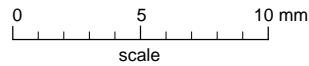
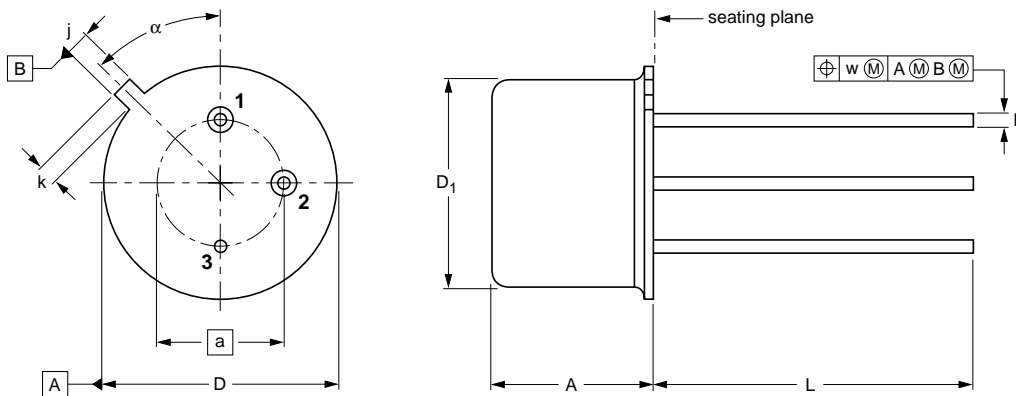
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PACKAGE OUTLINE

Metal-can cylindrical single-ended package; 3 leads

SOT5/11



DIMENSIONS (mm are the original dimensions)

UNIT	A	a	b	D	D ₁	j	k	L	w	α
mm	6.60 6.35	5.08	0.48 0.41	9.39 9.08	8.33 8.18	0.85 0.75	0.95 0.75	14.2 12.7	0.2	45°

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT5/11		TO-39				97-04-11

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DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

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NOTES

